

Day : Wednesday

Date: 8/31/2005

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PALM INTRANET
Inventor Name Search Result

Your Search was:

Last Name = SAXLER

First Name = ADAM

Application#	Patent#	Status	Date Filed	Title	Inventor Name
<u>11083460</u>	Not Issued	30	03/17/2005	LED with substrate modifications for enhanced light extraction and method of making same	SAXLER, ADAM W.
<u>10199454</u>	6841001	150	07/19/2002	STRAIN COMPENSATED SEMICONDUCTOR STRUCTURES AND METHODS OF FABRICATING STRAIN COMPENSATED SEMICONDUCTOR STRUCTURES	SAXLER, ADAM WILLIAM
<u>10199786</u>	Not Issued	71	07/19/2002	Strain balanced nitride heterojunction transistors	SAXLER, ADAM WILLIAM
<u>10378331</u>	Not Issued	92	03/03/2003	INTEGRATED NITRIDE-BASED ACOUSTIC WAVE DEVICES AND METHODS OF FABRICATING INTEGRATED NITRIDE-BASED ACOUSTIC WAVE DEVICES	SAXLER, ADAM WILLIAM
<u>10617843</u>	Not Issued	92	07/11/2003	NITRIDE-BASED TRANSISTORS AND METHODS OF FABRICATION THEREOF USING NON-ETCHED CONTACT RECESSES	SAXLER, ADAM WILLIAM
<u>10619228</u>	6875995	150	07/14/2003	HETEROGENEOUS BANDGAP STRUCTURES FOR SEMICONDUCTOR DEVICES AND MANUFACTURING METHODS THEREFOR	SAXLER, ADAM WILLIAM
<u>10640934</u>	Not Issued	83	08/14/2003	Nitrogen passivation of interface states in SiO ₂ /SiC structures	SAXLER, ADAM WILLIAM
<u>10707898</u>	Not Issued	71	01/22/2004	Silicon Carbide on Diamond Substrates and Related Devices and Methods	SAXLER, ADAM WILLIAM

<u>10752970</u>	Not Issued	71	01/07/2004	Co-doping for fermi level control in semi-insulating Group III nitrides	SAXLER, ADAM WILLIAM
<u>10772882</u>	Not Issued	30	02/05/2004	Nitride heterojunction transistors having charge-transfer induced energy barriers and methods of fabricating the same	SAXLER, ADAM WILLIAM
<u>10839593</u>	Not Issued	30	05/05/2004	Strain compensated semiconductor structures	SAXLER, ADAM WILLIAM
<u>10849589</u>	Not Issued	30	05/20/2004	Semiconductor devices having a hybrid channel layer, current aperture transistors and methods of fabricating same	SAXLER, ADAM WILLIAM
<u>10849617</u>	Not Issued	30	05/20/2004	Methods of fabricating nitride-based transistors having regrown ohmic contact regions and nitride-based transistors having regrown ohmic contact regions	SAXLER, ADAM WILLIAM
<u>10899215</u>	Not Issued	30	07/26/2004	Nitride-based transistors having laterally grown active region and methods of fabricating same	SAXLER, ADAM WILLIAM
<u>10996249</u>	Not Issued	30	11/23/2004	Cap layers and/or passivation layers for nitride-based transistors, transistor structures and methods of fabricating same	SAXLER, ADAM WILLIAM
<u>11005107</u>	Not Issued	30	12/06/2004	High power density and/or linearity transistors	SAXLER, ADAM WILLIAM
<u>11005423</u>	Not Issued	30	12/06/2004	Field effect transistors (FETs) having multi-watt output power at millimeter-wave frequencies	SAXLER, ADAM WILLIAM
<u>11073484</u>	Not Issued	30	03/03/2005	High electron mobility transistor	SAXLER, ADAM WILLIAM
<u>11080905</u>	Not Issued	30	03/15/2005	Group III nitride field effect transistors (FETS) capable of withstanding high temperature reverse bias test conditions	SAXLER, ADAM WILLIAM
<u>11103117</u>	Not Issued	30	04/11/2005	Thick semi-insulating or insulating epitaxial gallium nitride layers and devices incorporating same	SAXLER, ADAM WILLIAM
<u>11103127</u>	Not Issued	30	04/11/2005	Composite substrates of conductive and insulating or semi-insulating group III-nitrides for group III-nitride devices	SAXLER, ADAM WILLIAM
<u>11118575</u>	Not Issued	30	04/29/2005	Aluminum free group III-nitride based high electron mobility transistors and methods of	SAXLER, ADAM WILLIAM

				fabricating same	
<u>11118675</u>	Not Issued	30	04/29/2005	Binary group III-nitride based high electron mobility transistors and methods of fabricating same	SAXLER, ADAM WILLIAM
<u>11149664</u>	Not Issued	20	06/10/2005	Highly uniform group III nitride epitaxial layers on 100 millimeter diameter silicon carbide substrates	SAXLER, ADAM WILLIAM
<u>11169471</u>	Not Issued	19	06/29/2005	Low dislocation density group III nitride layers on silicon carbide substrates and methods of making the same	SAXLER, ADAM WILLIAM
<u>60331792</u>	Not Issued	159	11/20/2001	Semi-insulating interlayer structure	SAXLER, ADAM WILLIAM
<u>60337687</u>	Not Issued	159	12/03/2001	Strain balanced nitride heterojunction transistor	SAXLER, ADAM WILLIAM
<u>60396236</u>	Not Issued	159	07/16/2002	Contacts in a regrowth recess for nitride based transistors and methods of fabricating contacts for nitride based transistors using a regrowth recess	SAXLER, ADAM WILLIAM
<u>60403947</u>	Not Issued	159	08/16/2002	Heterogeneous bandgap structures for semiconductor devices and manufacturing methods therefor	SAXLER, ADAM WILLIAM
<u>60406753</u>	Not Issued	159	08/30/2002	Nitrogen passivation of interface states in SiO ₂ /SiC structures	SAXLER, ADAM WILLIAM

Inventor Search Completed: No Records to Display.

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